

180-

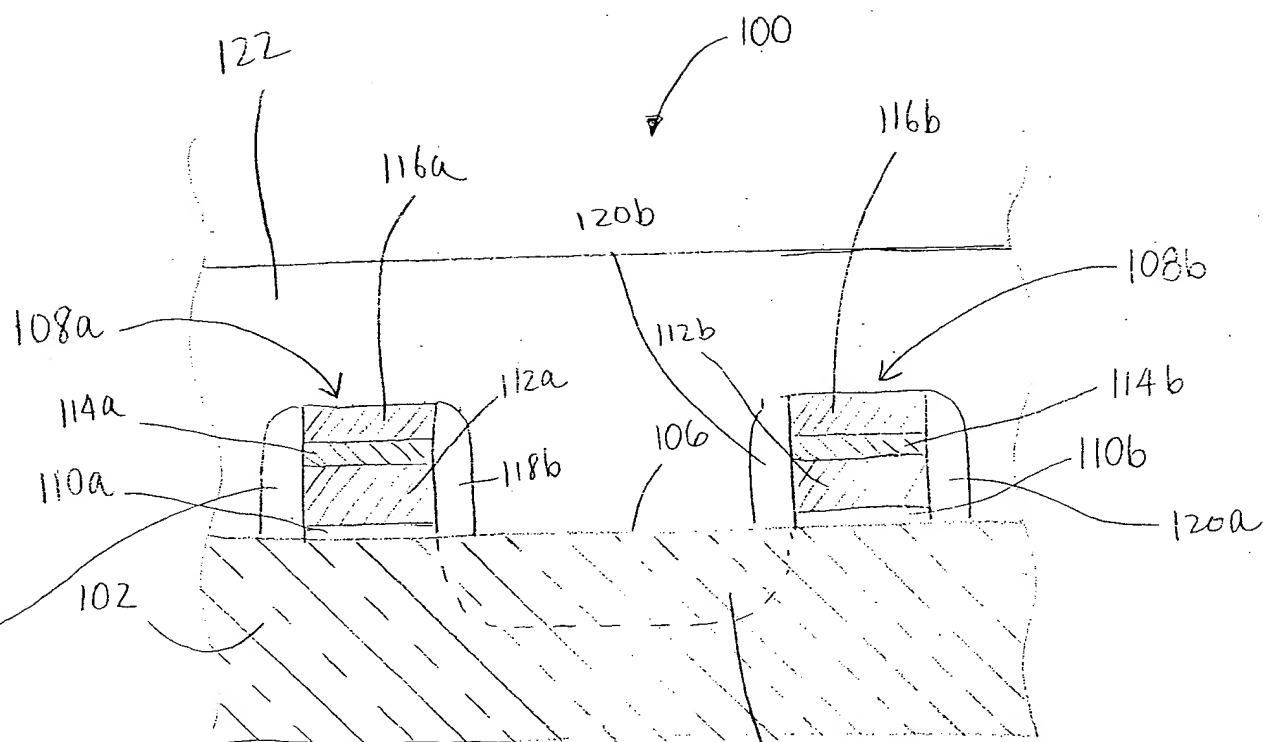


FIG 1

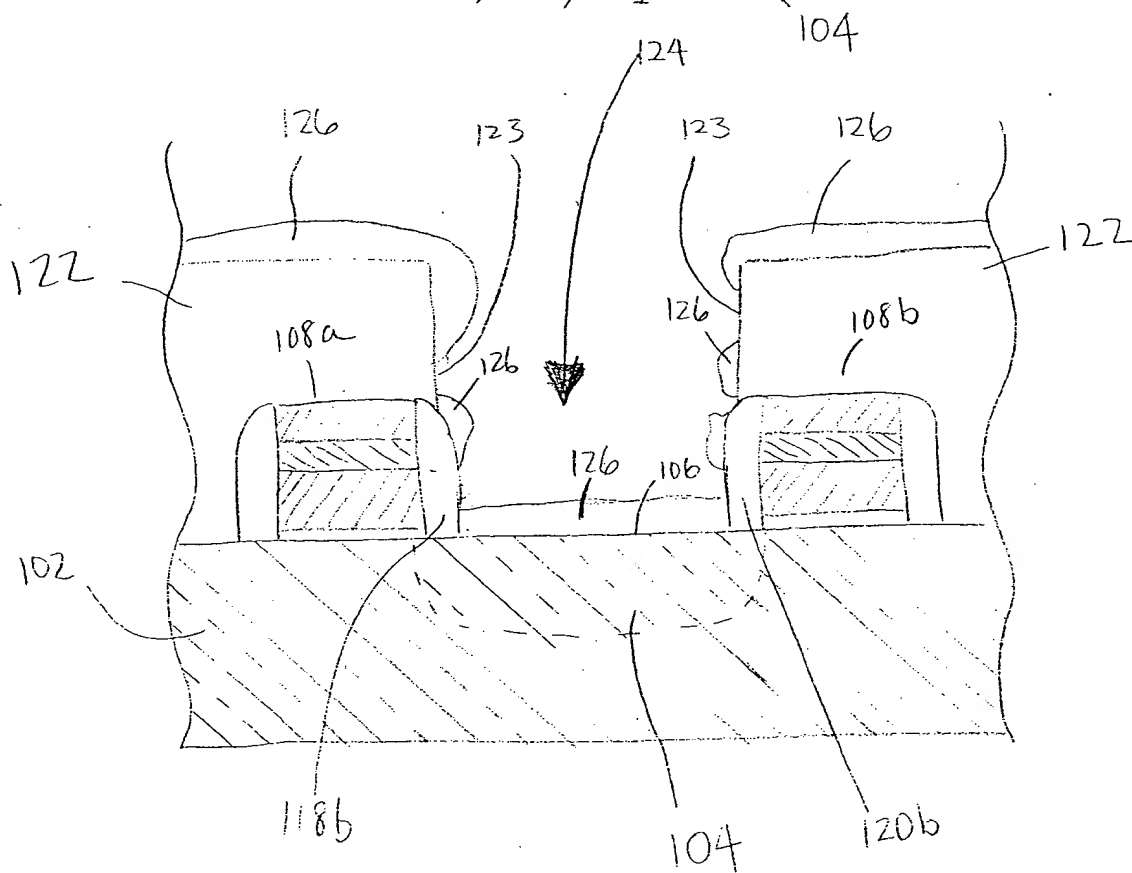


FIG. 2

FIG. 3

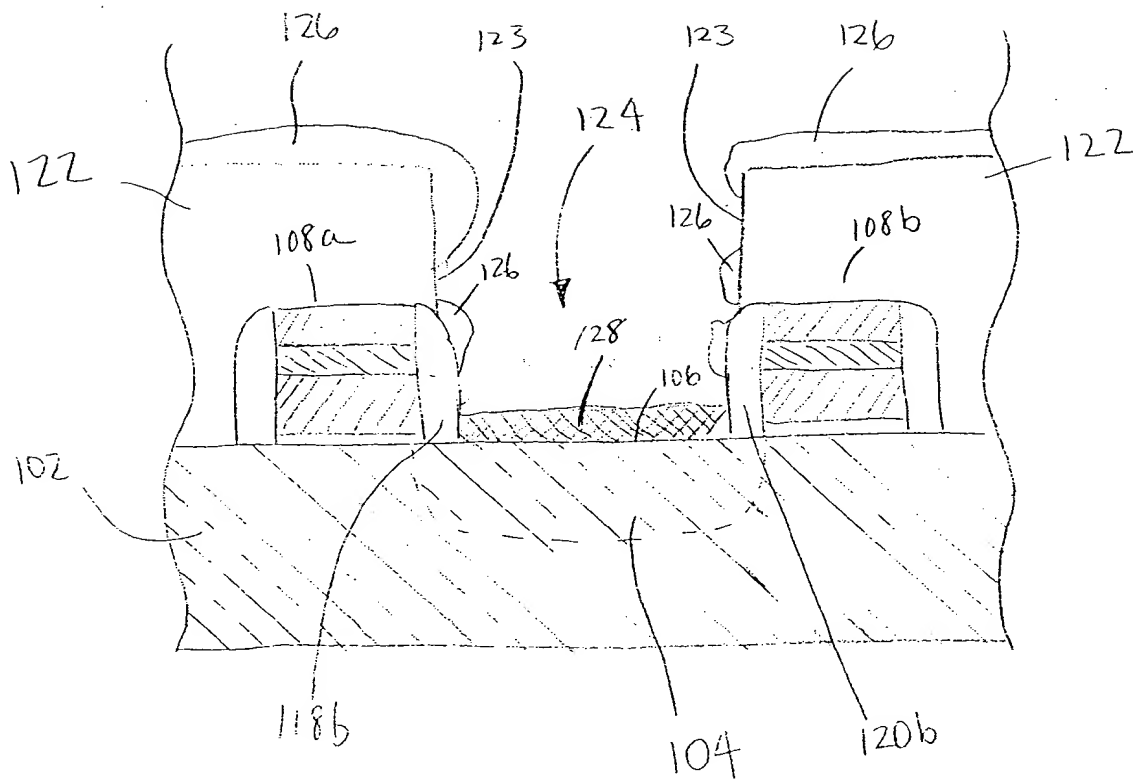


FIG. 3

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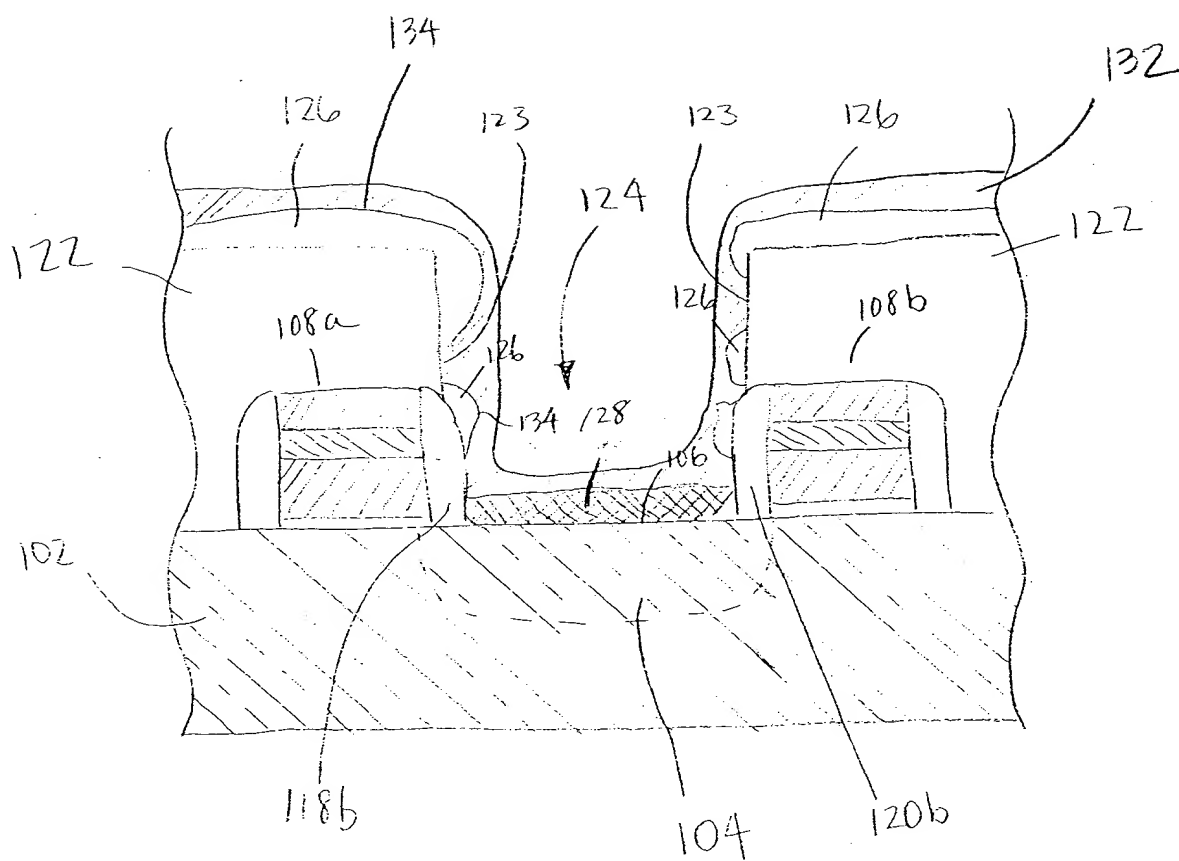


FIG 4

A cross-sectional view of a semiconductor device 100. The device is formed on a substrate 102. A base layer 104 is disposed on the substrate 102. A central trench 124 is formed in the base layer 104. The trench 124 has a bottom layer 128 and side layers 126. Two conductive regions 108a and 108b are located on either side of the trench 124. Various other layers and features are labeled with reference numerals: 100 (device), 102 (substrate), 104 (base layer), 108a and 108b (conductive regions), 122 (top layer), 123 (side wall), 124 (trench), 126 (side layer), 128 (bottom layer), 132 (top edge), 134 (side wall), 136 (top edge), 118b (bottom layer), 120b (side layer), 124 (trench), 126 (side layer), 128 (bottom layer), 134 (side wall), 136 (top edge).

FIG 5

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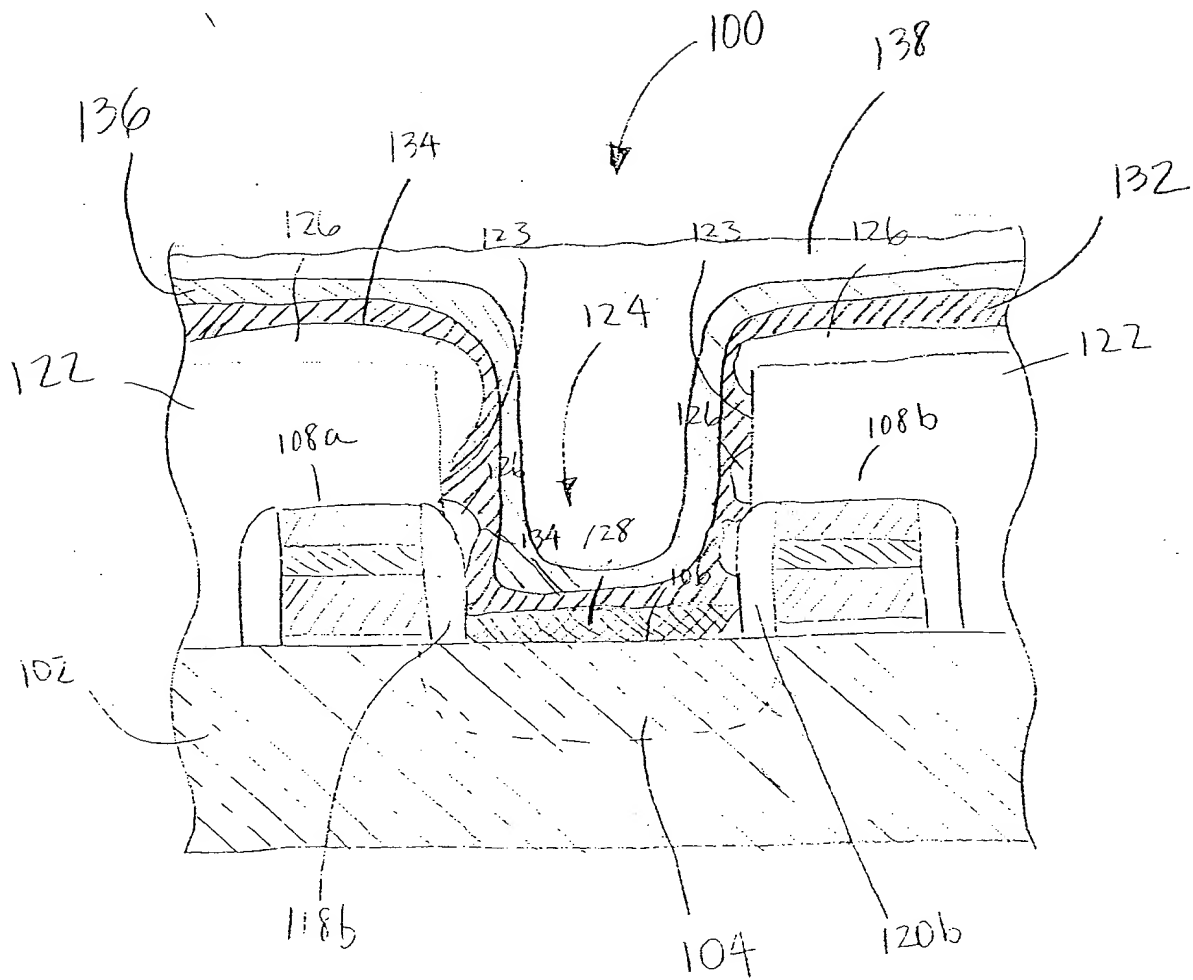


FIG. 6